

033035 M 0342

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Kensaku MOTOKI, et al.

U.S. Serial No.: 10/691,569

Group Art Unit: 2814

Filed: October 24, 2003

Examiner: To Be Assigned

For: GaN Single Crystal Substrate and Method of Making the Same

THIRD INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:


Pursuant to the duty of disclosure under 37 C.F.R. 1.56, Applicants enclose an Information Disclosure Citation Form (PTO-1449) which lists documents cited in a Japanese Office Action (dated April 18, 2006) submitted herewith.

Applicants certify under 37 C.F.R. 1.97(e)(1) that all documents submitted herewith were first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement. Therefore, it is respectfully urged that no fees are required for the Examiner's consideration of the documents listed in this Information Disclosure Statement.

It is respectfully requested that the cited documents be considered by the Examiner in the above-identified patent application and that the cited documents be made officially of record therein. It is further requested that a listing of the same appear on the face of any patent which may issue from this application.

Respectfully submitted,
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By:


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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET 033035 M 0342	SERIAL NO. 10/691,569
	APPLICANT: Kensaku MOTOKI, et al.	
	FILING DATE October 24, 2003	GROUP ART UNIT 2814

U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES NO	
	AL	97/11518	3/27/1997	WO				
	AM	07-273048	10/20/1995	JAPAN			abstract	
	AN	11-135770	5/21/1999	JAPAN			abstract	
	AO							
	AP							

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

AQ	H. Okumura, et al., "Epitaxial growth of cubic and hexagonal GaN on GaAs by gas-source molecular-beam epitaxy", Appl. Phys. Lett. 59(9), August 26, 1991, pages 1058-1060, November 2002
AR	K. Naniwae, et al., "Growth of Single Crystal GaN Substrate Using Hydride Vapor Phase Epitaxy", Journal of Crystal Growth 99, 1990, pages 381-384
AS	Notice of Rejection from JPO
EXAMINER:	DATE CONSIDERED:
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	